Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Extended temperature range T_i = 175 °C
- · Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · High-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V	
V_{GS}	gate-source voltage			-12	-	12	V	
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-5.2	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -5.2 \text{ A}; T_j = 25 \text{ °C}$		-	30	38	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	Д6 Д5 Д4	D
2	D	drain		
3	G	gate	<u> 0</u>	G (F)
4	S	source	SC-74; TSOP6 (SOT457)	s
5	D	drain	, , ,	017aaa094
6	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN30XPA	SC-74; TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN30XPA	3T

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-5.2	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-3.3	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-21	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	660	mW
			[1]	-	1.7	W
		T _{sp} = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain o	liode		'	'		
Is	source current	T _{amb} = 25 °C	[1]	-	-1.7	Α
ESD maximum	rating		'	'		
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	500	V
Avalanche rug	gedness	,		1		,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -1.5 A; DUT in avalanche (unclamped)		-	15.5	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

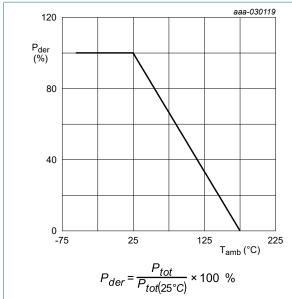


Fig. 1. Normalized total power dissipation as a function of ambient temperature

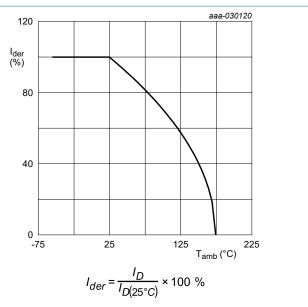


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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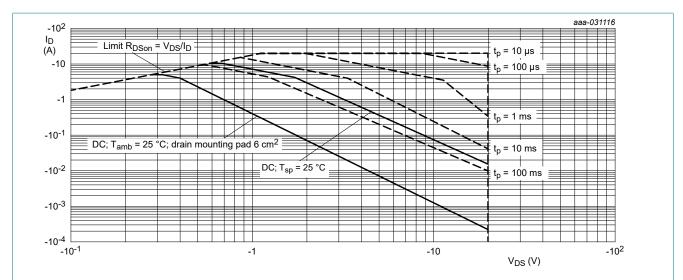


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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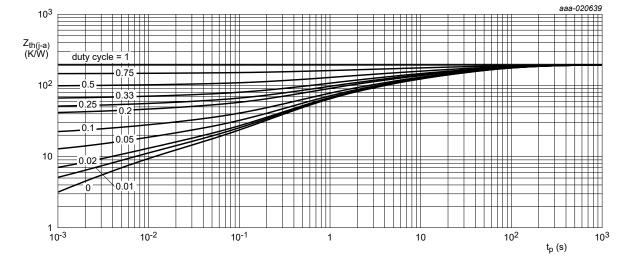
20 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

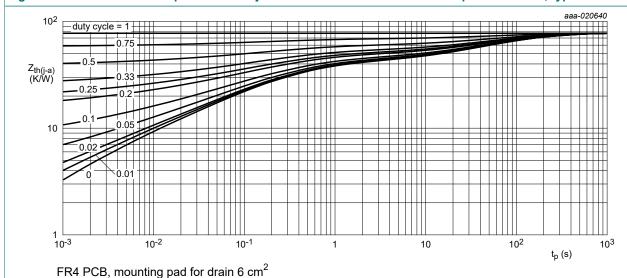
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	195	225	K/W
junction to an	junction to ambient		[2]	-	78	90	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.6	-0.95	-1.3	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -8 \text{ V}; I_D = -5.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	25	33	mΩ
	resistance	V _{GS} = -8 V; I _D = -5.2 A; T _j = 175 °C	-	40	53	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -5.2 \text{ A}; T_j = 25 \text{ °C}$	-	30	38	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	45	62	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -4.9 \text{ A}; T_j = 25 \text{ °C}$	-	18	-	S
R _G	gate resistance	f = 1 MHz	-	6	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -5 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	11	16	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.9	-	nC
Q_{GD}	gate-drain charge		-	3.4	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	1039	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	124	-	pF
C _{rss}	reverse transfer capacitance		-	110	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -10 \text{ V}; I_D = -5 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	40	-	ns
t _f	fall time		-	23	-	ns
Source-drai	in diode		'			
V_{SD}	source-drain voltage	$I_S = -1.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.8	-1.2	V
t _{rr}	reverse recovery time	$I_S = -1.5 \text{ A}$; $dI_S/dt = 100 \text{ A/µs}$;	-	13	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	3	-	nC

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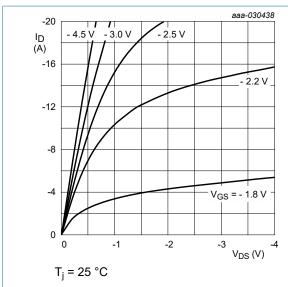


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

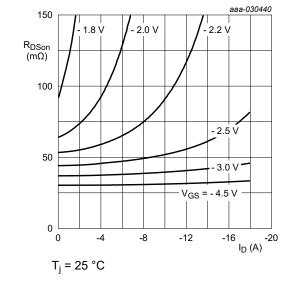


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

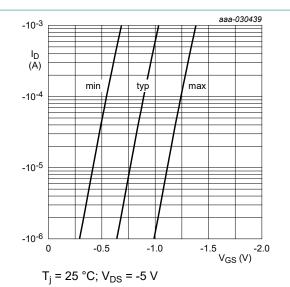


Fig. 7. Subthreshold drain current as a function of gate-source voltage

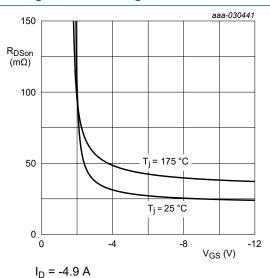


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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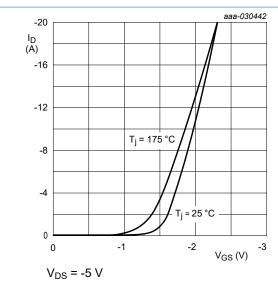


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

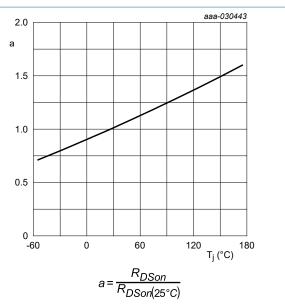


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

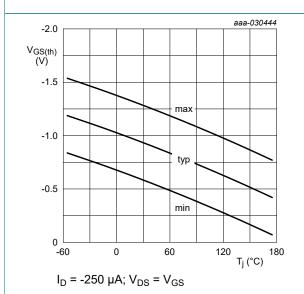
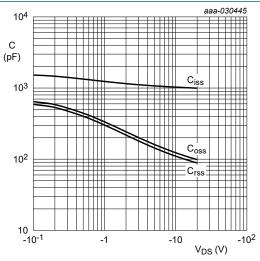


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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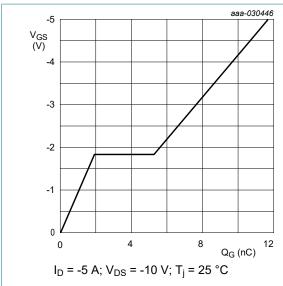


Fig. 14. Gate-source voltage as a function of gate charge; typical values

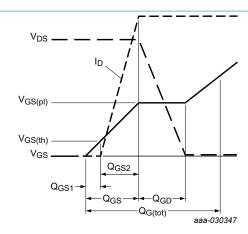


Fig. 15. Gate charge waveform definitions

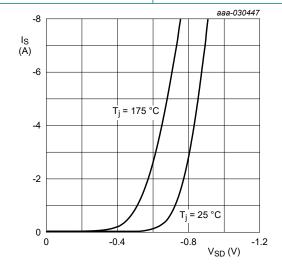
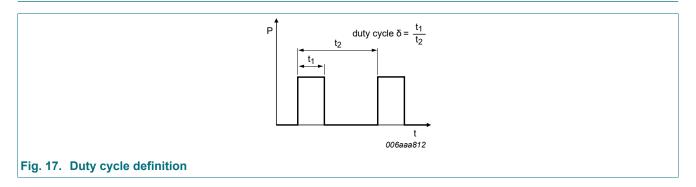


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

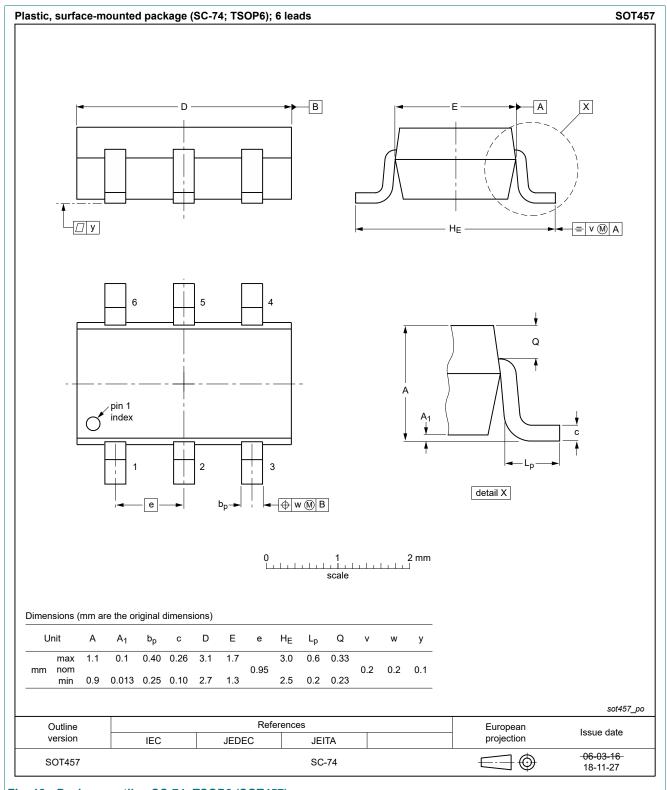
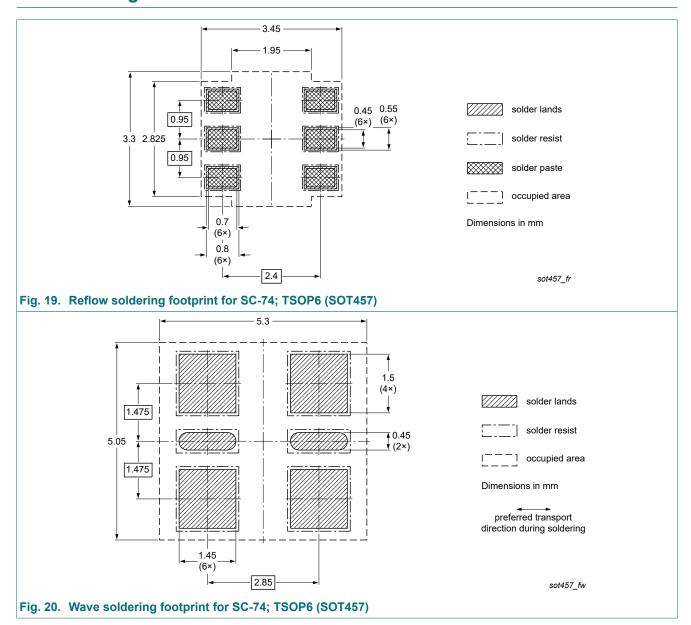


Fig. 18. Package outline SC-74; TSOP6 (SOT457)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN30XPA v.1	20200420	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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